

**Amendment to the Claims**

Please amend the Claims as follows and without prejudice. This listing of Claims will replace all prior versions, and listings, of claims in the application.

**Listing of Claims:**

1. (CURRENTLY AMENDED) A method for forming a semiconductor material from powders comprising at least one component belonging to the group formed by the elements of column IV of the Mendeleiev table and their alloys, said method comprising: ~~a step~~ one or more steps of compression of said powders; and one or more[[a]] thermal processing steps [[step]] such that [[part]] at least part of the powders is melted or made viscous, wherein, at least one of the one or more compression steps and at least one of the one or more thermal processing steps are simultaneous.
2. (CANCELLED)
3. (CURRENTLY AMENDED) The method of claim 1, wherein at least one of the one or more thermal processing steps is such that only powders belonging to a specific area of the material are melted or made viscous.
4. (PREVIOUSLY PRESENTED) The method of claim 1, wherein the powders comprise silicon powders and powders of at least another component, the thermal processing being such that the silicon is not melted and that at least one of the other components is melted or made viscous.

5. (PREVIOUSLY PRESENTED) The method of claim 1, wherein the powders comprise doped semiconductor powders and undoped semiconductor powders, the thermal processing being such that only the doped powders are melted.
6. (PREVIOUSLY PRESENTED) The method of claim 1, wherein the compression step is preceded by a step consisting of placing powders on a plate, the powders being different as to at least one of their nature, their granulometry, and their doping according to their location on the plate.
7. (CURRENTLY AMENDED) The method of claim 1, wherein during the compression step, said powders are pressed between plates having a surface capable of texturizing the surface of the material.
8. (PREVIOUSLY PRESENTED) A semiconductor material obtained at least partially by compression and thermal processing of powders comprising at least two distinct areas formed of distinct components belonging to the group formed by the elements of column IV of the Mendeleiev table and the alloys thereof.
9. (ORIGINAL) The material of claim 8, wherein said areas are superposed.
10. (ORIGINAL) A structure or a component formed of one or comprising at least one semiconductor material comprising grains and/or aggregates exhibiting energy gaps of different value.
11. (NEW) A method for forming a semiconductor material from powders comprising at least one component belonging to the group formed by the elements of column IV of the Mendeleiev table and their alloys, said method comprising a step of compression of said powders and a thermal processing step such that at least part of the powders is melted or made viscous,

wherein the thermal processing is such that only powders belonging to a specific area of the material are melted or made viscous.

12. (NEW) A method for forming a semiconductor material from powders comprising at least one component belonging to the group formed by the elements of column IV of the Mendeleiev table and their alloys, said method comprising a step of compression of said powders and a thermal processing step such that at least part of the powders is melted or made viscous,

wherein the powders comprise silicon powders and powders of at least another component, the thermal processing being such that the silicon is not melted and that at least one of the other components is melted or made viscous.

13. (NEW) A method for forming a semiconductor material from powders comprising at least one component belonging to the group formed by the elements of column IV of the Mendeleiev table and their alloys, said method comprising a step of compression of said powders and a thermal processing step such that at least part of the powders is melted or made viscous,

wherein the powders comprise doped semiconductor powders and undoped semiconductor powders, the thermal processing being such that only the doped powders are melted.

14. (NEW) A method for forming a semiconductor material from powders comprising at least one component belonging to the group formed by the elements of column IV of the Mendeleiev table and their alloys, said method comprising a step of

compression of said powders and a thermal processing step such that at least part of the powders is melted or made viscous,

wherein the compression step is preceded by a step consisting of placing powders on a plate, the powders being different as to at least one of their nature, their granulometry, and their doping according to their location on the plate.